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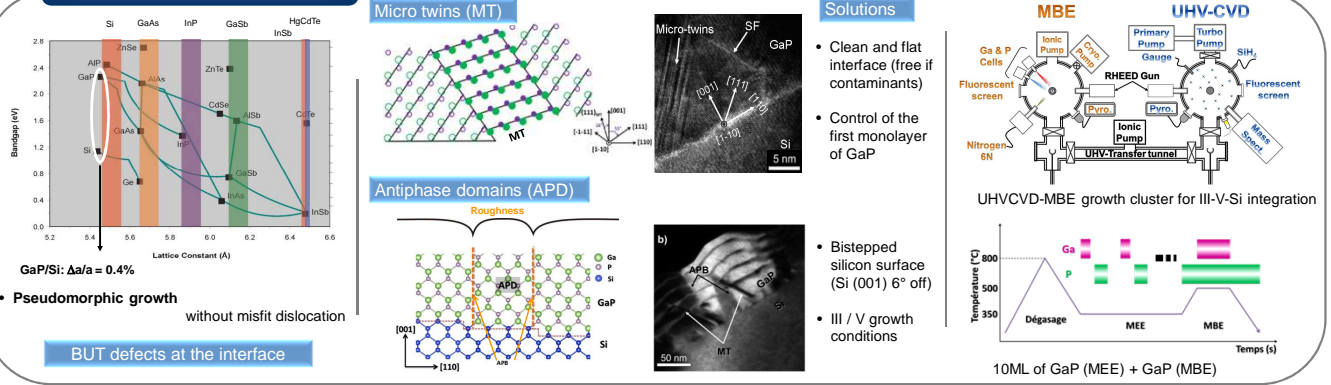
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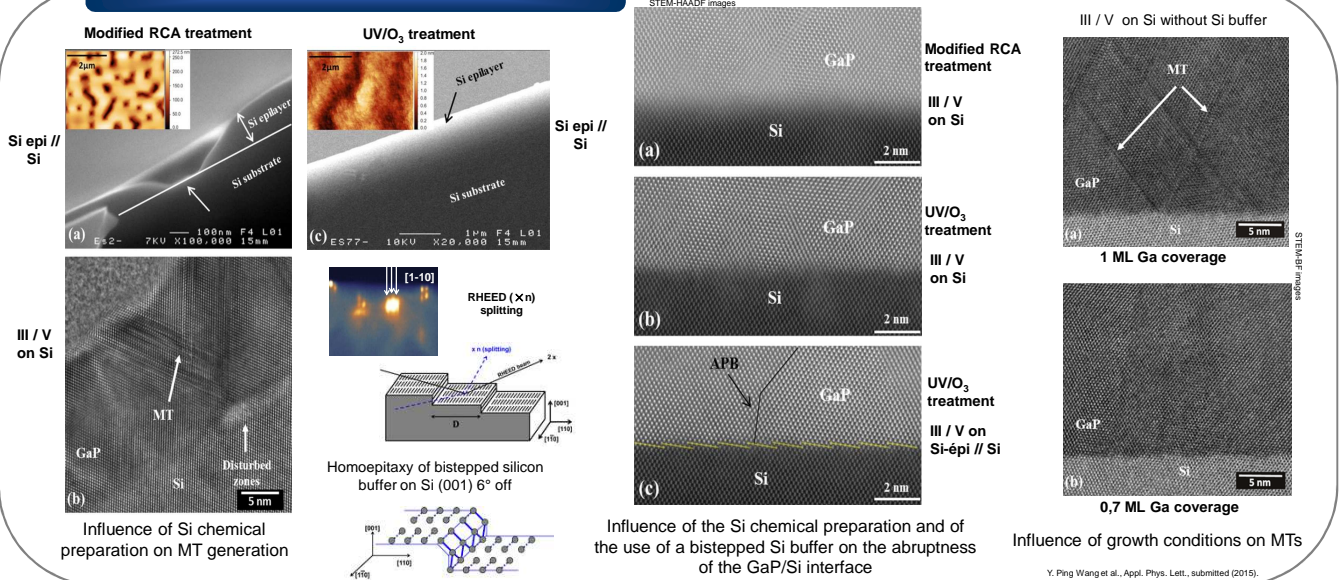
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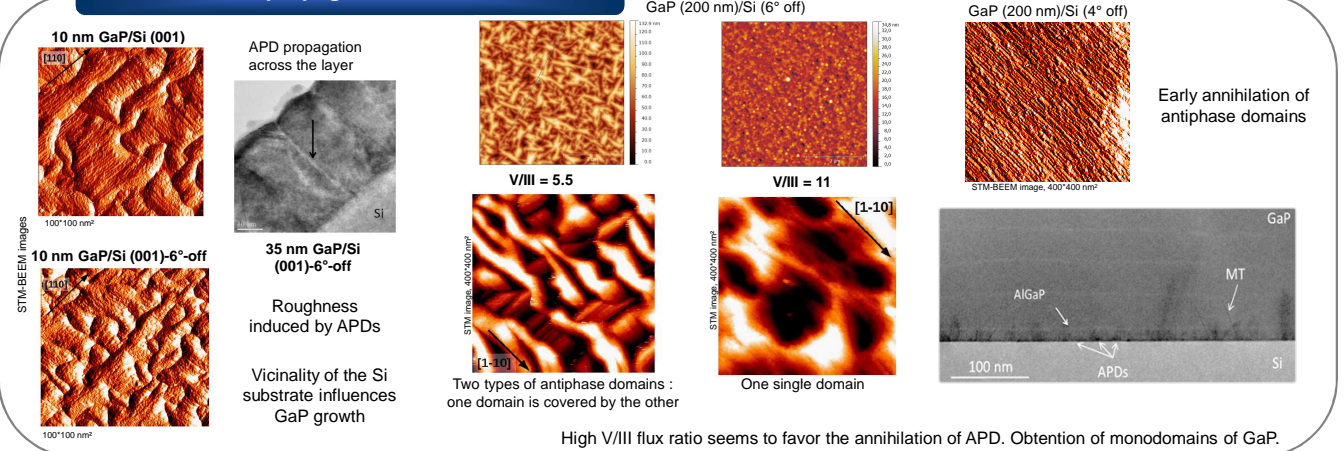
Introduction



GaP/Si interface : MT generation, and abruptness



Influence of APB propagation and V/III flux ratio



Conclusions & Perspectives

- MTs and abruptness of GaP/Si interface : sensitive to chemical preparation and improved by the use of a bisteped Si buffer . BUT antiphase boundaries are still observable.
 - High V/III flux ratio tends to favor APD annihilation at the early stages of growth.
- Perspectives :** Detailed study of the influence of the growth parameters is required to understand these observations (ANR Antipode).

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